# P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)			
- 60	$0.0208$ at $V_{GS} = -10 \text{ V}$	- 66	76 nC			
	0.0263 at V <sub>GS</sub> = - 4.5 V	- 52	70110			

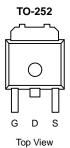
#### **FEATURES**

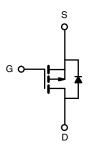
- TrenchFET® Power MOSFET
- 100 % UIS Tested

#### **APPLICATIONS**

Load Switch







P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATING</b>	<b>S</b> (T <sub>A</sub> = 25 °C, unle	ess otherwise not	ed)	
Parameter	Symbol Limit		Unit	
Drain-Source Voltage	V <sub>DS</sub>	- 60	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20	V	
	T <sub>C</sub> = 25 °C		- 66 <sup>a</sup>	
Continuous Drain Current (T. – 150 °C)	T <sub>C</sub> = 70 °C		- 46.8	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	9.2 <sup>b</sup>	
	T <sub>A</sub> = 70 °C		- 8.1 <sup>b</sup>	A
Pulsed Drain Current	I <sub>DM</sub>	- 180		
Avalanche Current Pulse	1 0.1 ml l	I <sub>AS</sub>	- 35	
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	101	mJ
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C		29 <sup>a</sup>	
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	2.1 <sup>b</sup>	A
	T <sub>C</sub> = 25 °C		104.2 <sup>a</sup>	
Mandagara Barras Birada di an	T <sub>C</sub> = 70 °C	В	66.7 <sup>a</sup>	, , , , , , , , , , , , , , , , , , ,
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.1 <sup>b</sup>	W
	T <sub>A</sub> = 70 °C		2 <sup>b</sup>	
Operating Junction and Storage Temperature R	T <sub>J</sub> , T <sub>stq</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b</sup>	Steady State	R <sub>thJA</sub>	33	40	°C/W	
Maximum Junction-to-Case	Steady State	R <sub>thJC</sub>	0.98	1.2	C/VV	

#### Notes:

- a. Based on  $T_C$  = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 60			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Γ <sub>J</sub>		68		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = - 250 μA		- 5.2		mv/·C	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
7 0 1 1/1 5 1 0 1	I <sub>DSS</sub>	V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current		V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	- 10		- 10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 120			Α	
D : 0	В	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 30 A		0.0208	0.0231	0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 20 A		0.0263	0.0298	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 50 A	20			S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			3500		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		390			
Reverse Transfer Capacitance	C <sub>rss</sub>			290			
Total Gata Chargo	Qg	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -55 \text{ A}$		76	76 115		
Total Gate Charge				38	60	nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -55 \text{ A}$		16			
Gate-Drain Charge	$Q_{gd}$			19			
Gate Resistance	$R_g$	f = 1 MHz		5.2		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			10	15		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 2 V, $R_L$ = 2 $\Omega$		7	15	ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 10 A, $V_{GEN} =$ - 10 V, $R_g = 1 \Omega$		70	110		
Fall Time	t <sub>f</sub>			40	60		
<b>Drain-Source Body Diode Characteristic</b>	S						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 66	Α	
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				- 180	^	
Body Diode Voltage	$V_{SD}$	I <sub>S</sub> = - 30 A		- 1	- 1.5	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			45	68	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = - 50 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C		59	120	nC	
Reverse Recovery Fall Time	t <sub>a</sub>			29		20	
Reverse Recovery Rise Time	t <sub>b</sub>			16		ns	

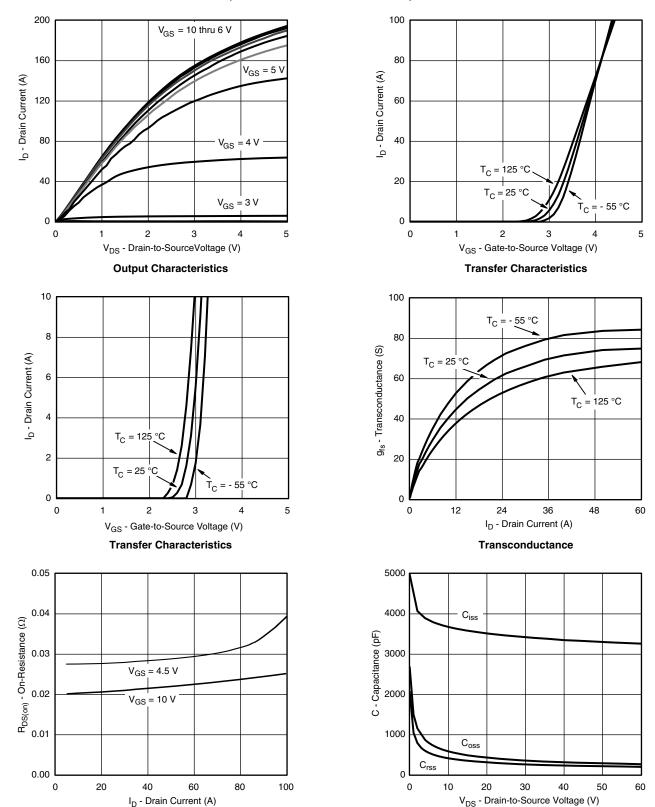
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

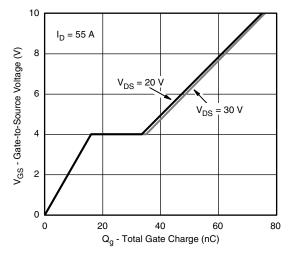
On-Resistance vs. Drain Current



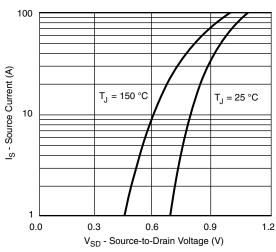
Capacitance



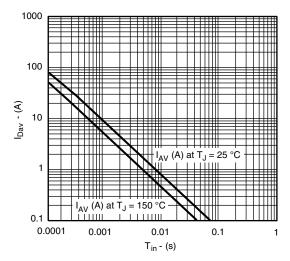
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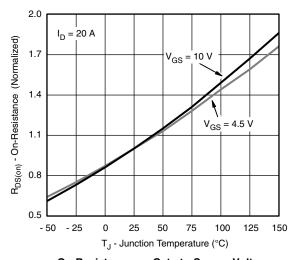
#### **Gate Charge**



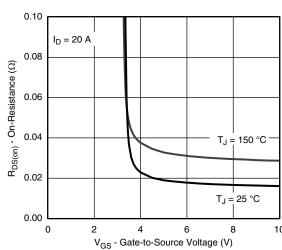
Source-Drain Diode Forward Voltage



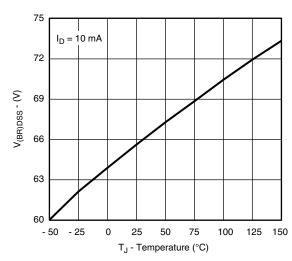
Single Pulse Avalanche Current Capability vs. Time



On-Resistance vs. Gate-to-Source Voltage

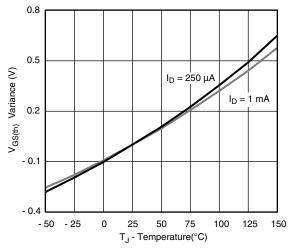


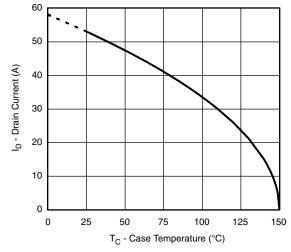
On-Resistance vs. Gate-to-Source Voltage



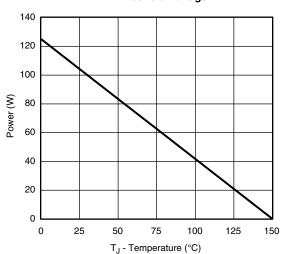
Drain-Source Breakdown Voltage vs. Junction Temperature

#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

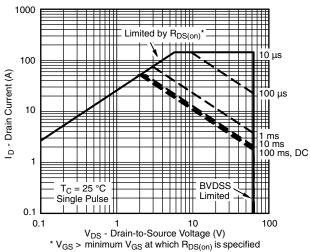




Threshold Voltage

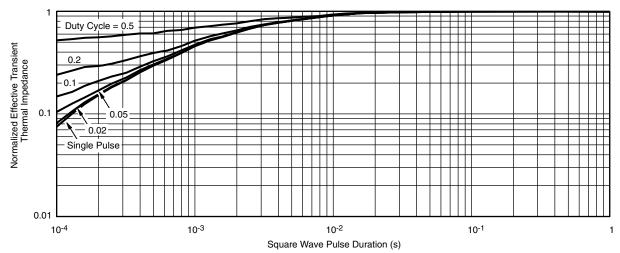


Max. Drain Current vs. Case Temperature



#### Power Derating, Junction-to-Case



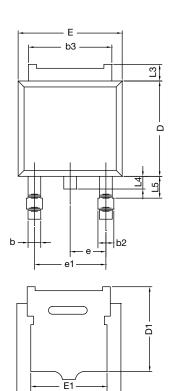


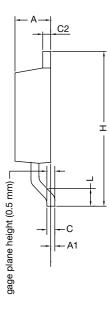
Normalized Thermal Transient Impedance, Junction-to-Case





## **TO-252AA CASE OUTLINE**





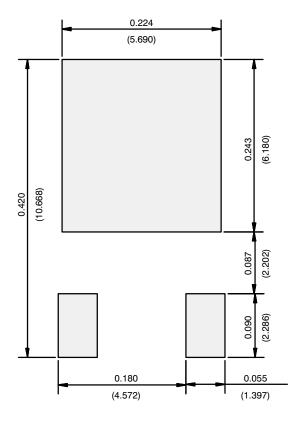
	MILLIN	METERS	INCHES			
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	5.21	-	0.205	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28	BSC	0.090	0.090 BSC		
e1	4.56 BSC		0.180	BSC		
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.14	1.52	0.045	0.060		
ECN: X12-0247-Rev. M, 24-Dec-12						

### DWG: 5347 Note

• Dimension L3 is for reference only.



### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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